

N-Channel Enhancement Mode Power MOSFET

Description

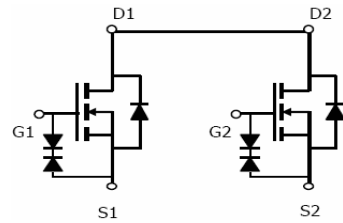
The PE6986E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

General Features

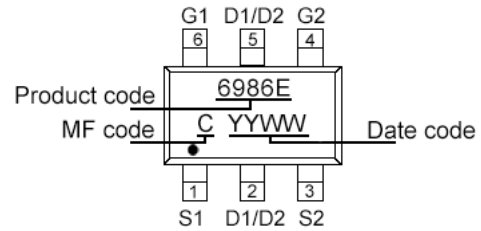
- $V_{DS} = 20V, I_D = 6.5A$
 - $R_{DS(ON)} < 15m\Omega @ V_{GS}=4.5V$
 - $R_{DS(ON)} < 16m\Omega @ V_{GS}=3.8V$
 - $R_{DS(ON)} < 20m\Omega @ V_{GS}=2.5V$
- ESD Rating: 2000V HBM
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM application
- Load switch



Schematic diagram



Marking and pin Assignment



SOT23-6 top view

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	6.5	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	83.3	$^\circ C/W$
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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$	-	-	1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.75	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=6.5A$	12	13	15	m Ω
		$V_{GS}=3.8V, I_D=6.0A$	12.5	13.5	16	m Ω
		$V_{GS}=2.5V, I_D=5.5A$	15.5	17	20	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=6A$	-	20	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	750	-	PF
Output Capacitance	C_{oss}		-	110	-	PF
Reverse Transfer Capacitance	C_{rss}		-	80	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=16V, R_L=1.5\Omega$ $V_{GS}=4.5V, R_{GEN}=3\Omega$ $I_{DS}=3A$	-	15		nS
Turn-on Rise Time	t_r		-	10		nS
Turn-Off Delay Time	$t_{d(off)}$		-	20		nS
Turn-Off Fall Time	t_f		-	30		nS
Total Gate Charge	Q_g	$V_{DS}=16V, I_{DS}=3A,$ $V_{GS}=4.5V$ $I_{DS}=3A$	-	12		nC
Gate-Source Charge	Q_{gs}		-	4	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V_{SD}	$V_{GS}=0V, I_{DS}=1A$	0.4	-	1.0	V
Diode Forward Current <small>(Note 2)</small>	I_S		-	-	6	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

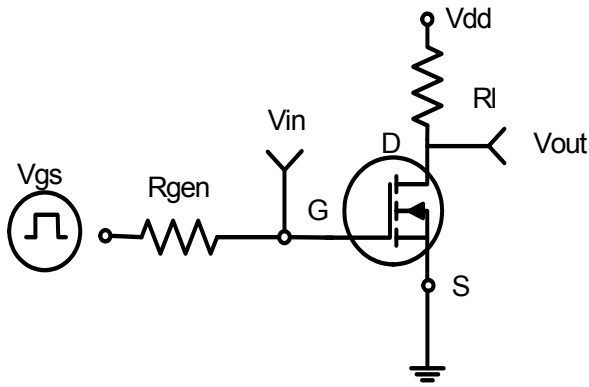


Figure 1: Switching Test Circuit

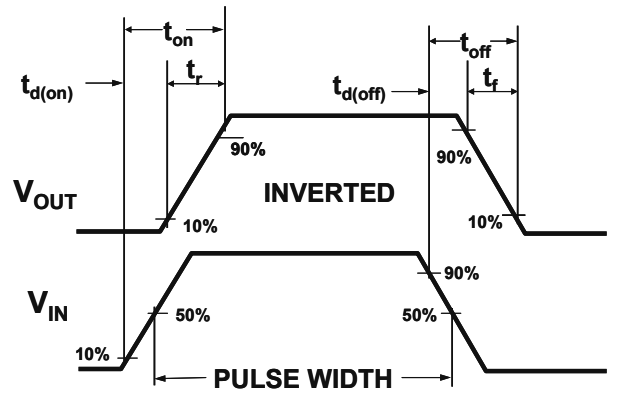


Figure 2: Switching Waveforms

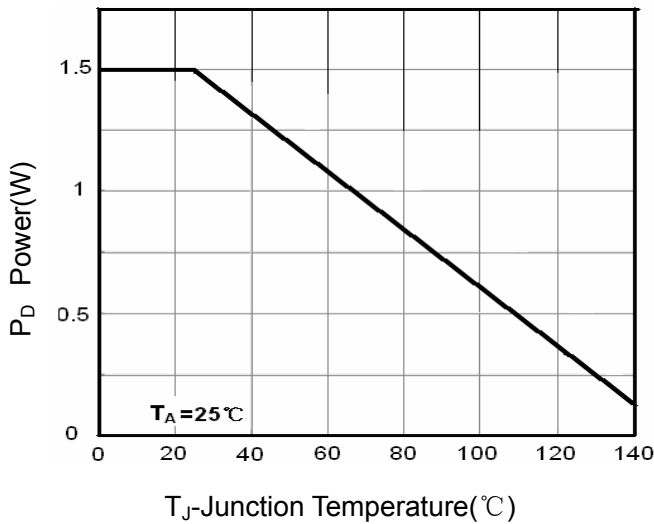


Figure 3 Power Dissipation

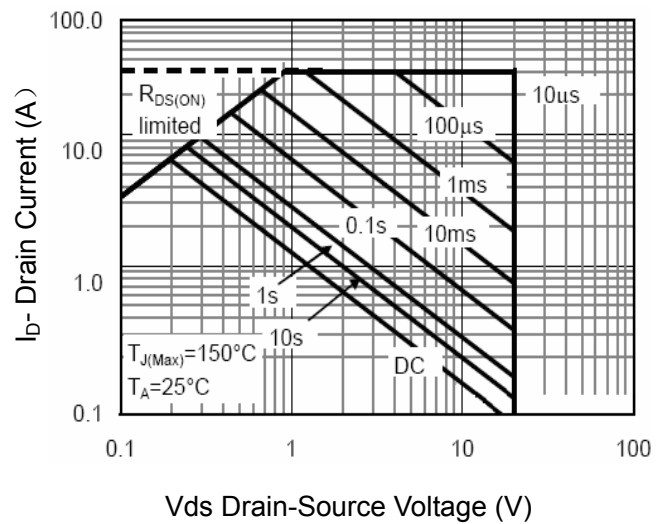


Figure 4 Safe Operation Area

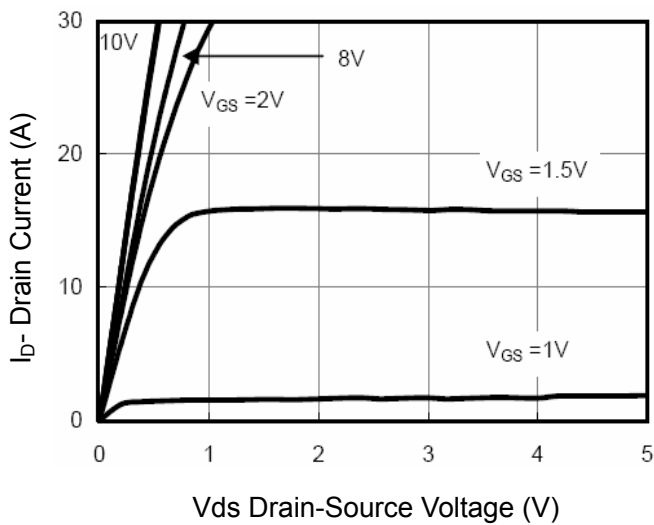


Figure 5 Output Characteristics

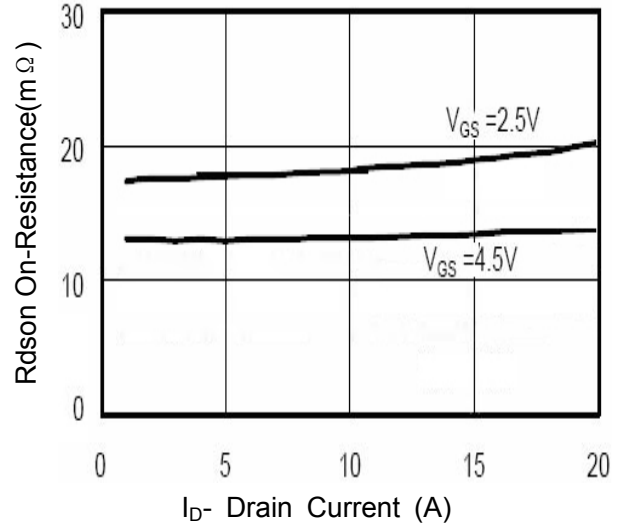


Figure 6 Drain-Source On-Resistance

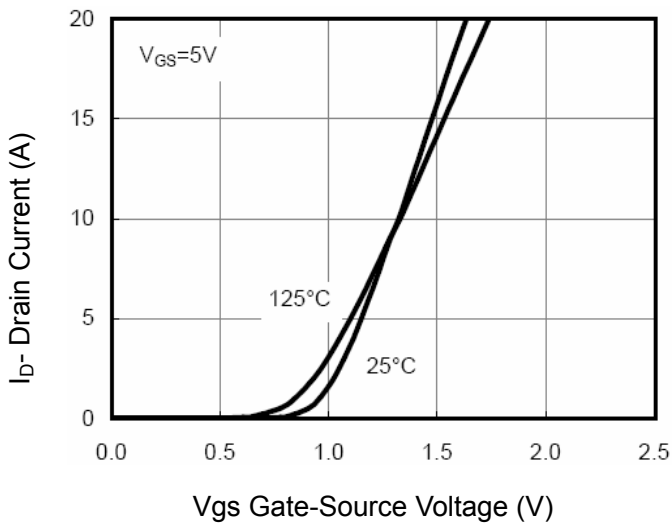


Figure 7 Transfer Characteristics

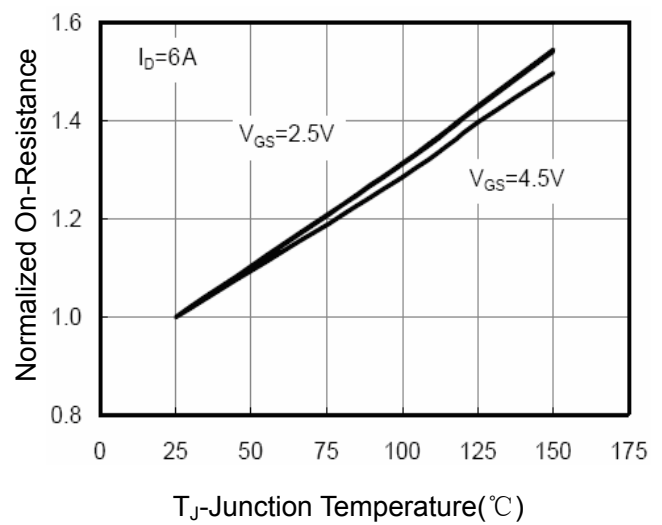


Figure 8 Drain-Source On-Resistance

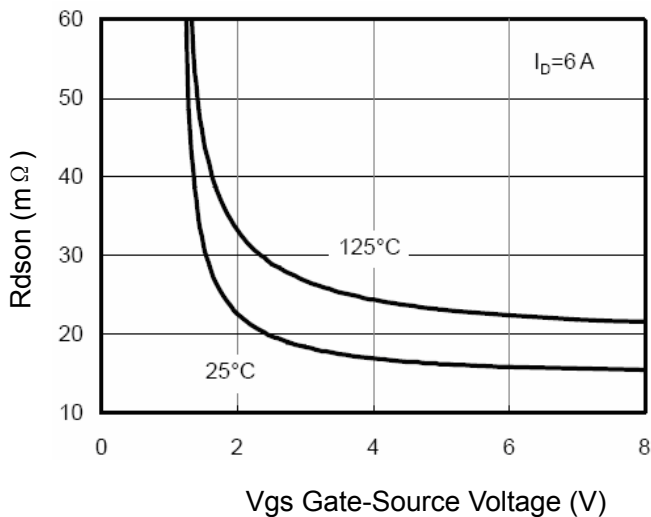


Figure 9 Rdson vs VGS

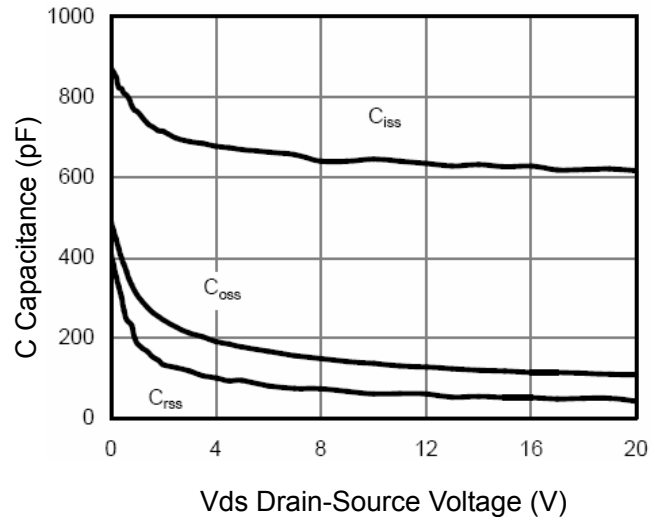


Figure 10 Capacitance vs Vds

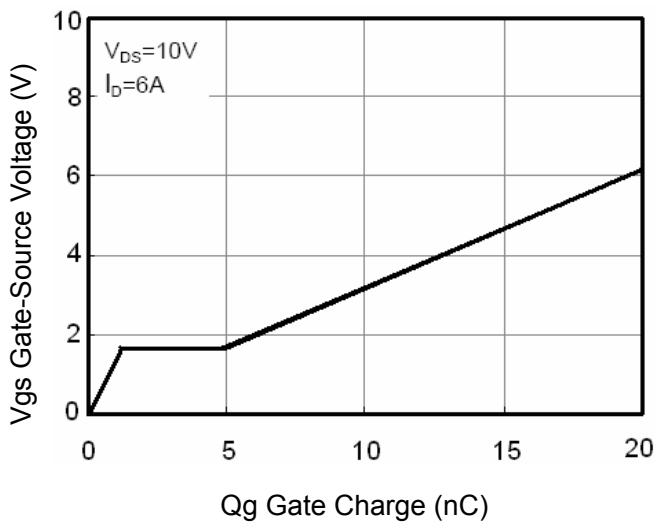


Figure 11 Gate Charge

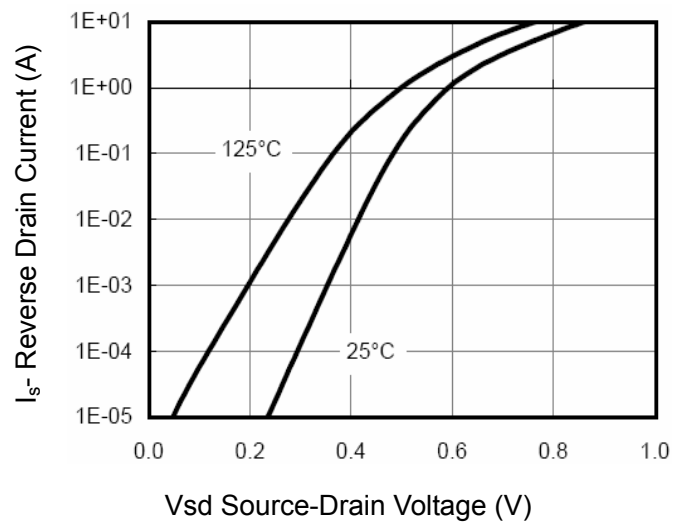


Figure 12 Source- Drain Diode Forward

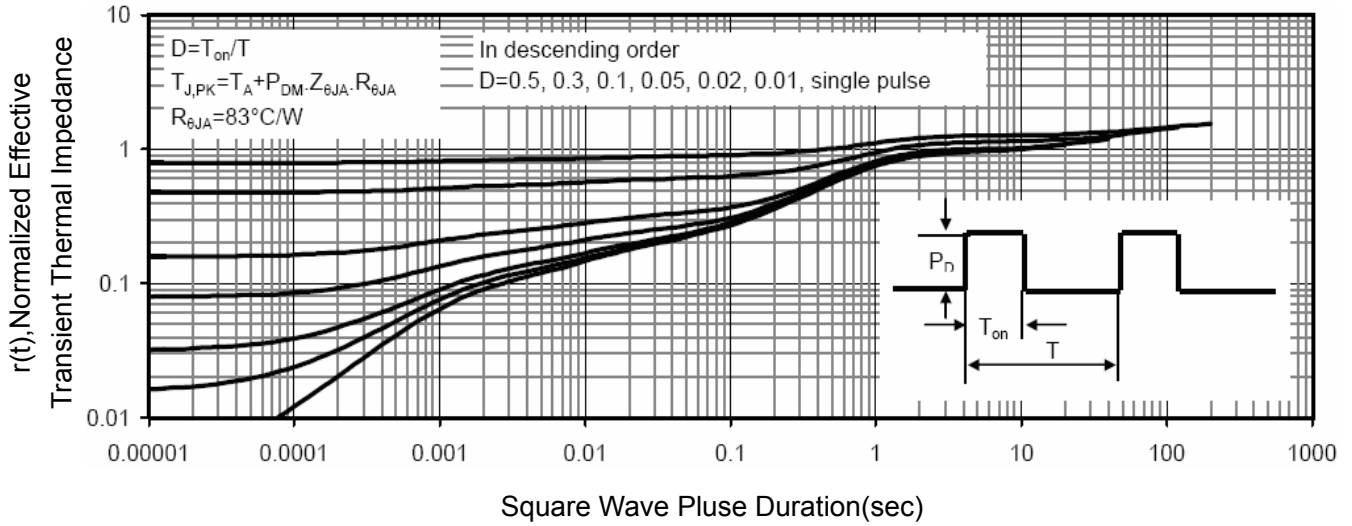


Figure 13 Normalized Maximum Transient Thermal Impedance

SOT23-6 PACKAGE INFORMATION

